



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



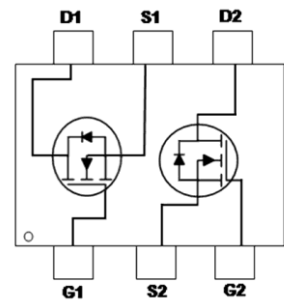
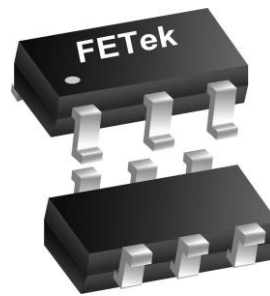
BVDSS	R _{DS(on)}	I _D
30V	33mΩ	4.6A

Description

The FKQ3208 is the high cell density trenched N-ch MOSFETs, which provides excellent R_{DS(on)} and efficiency for most of the small power switching and load switch applications.

The FKQ3208 meet the RoHS and Green Product requirement with full function reliability approved.

TSOP6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.6	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	3.7	A
I _{DM}	Pulsed Drain Current ²	18.4	A
P _D @T _A =25°C	Total Power Dissipation ³	1	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	125	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	80	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.023	---	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=4A$	---	27	33	m Ω
		$V_{GS}=4.5V, I_D=3A$	---	36	50	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.2	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=4A$	---	7	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	2.3	4.6	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=4A$	---	5.0	6.9	nC
Q_{gs}	Gate-Source Charge		---	1.1	2.2	
Q_{gd}	Gate-Drain Charge		---	2.6	2.8	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=4A$	---	2	4	ns
T_r	Rise Time		---	34.4	62	
$T_{d(off)}$	Turn-Off Delay Time		---	13.2	26	
T_f	Fall Time		---	4.8	9.6	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	420	582	pF
C_{oss}	Output Capacitance		---	60	87	
C_{rss}	Reverse Transfer Capacitance		---	53	71	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	4.6	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	18.4	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=4A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	8.7	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.3	---	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

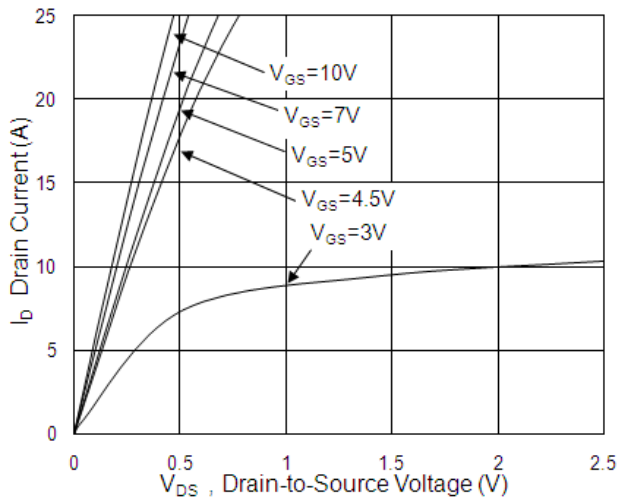


Fig.1 Typical Output Characteristics

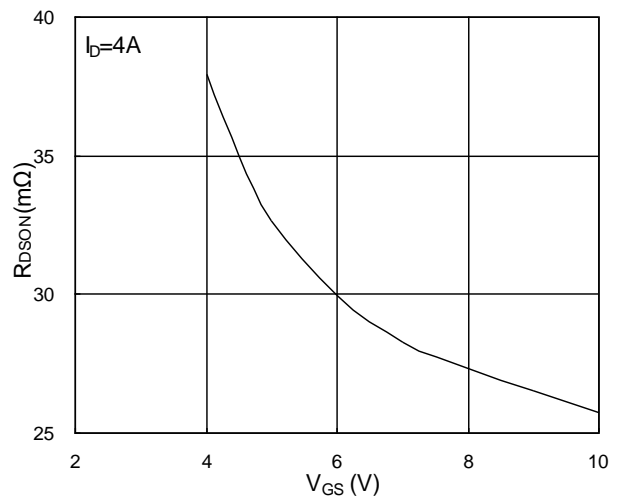


Fig.2 On-Resistance vs G-S Voltage

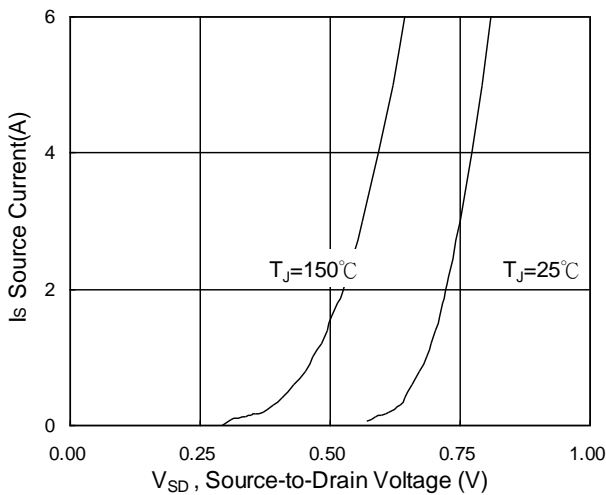


Fig.3 Source Drain Forward Characteristics

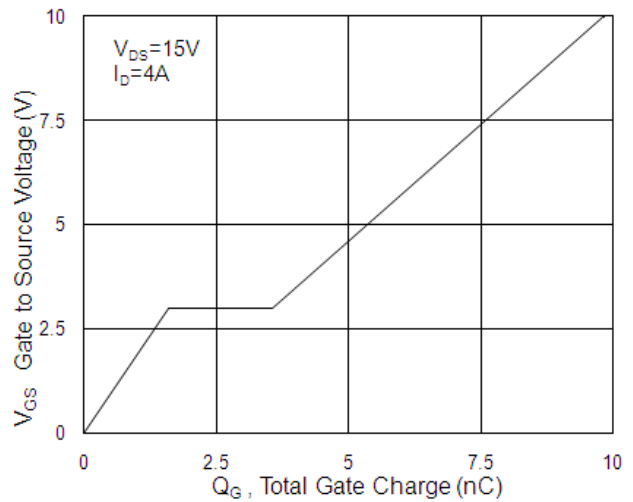


Fig.4 Gate-Charge Characteristics

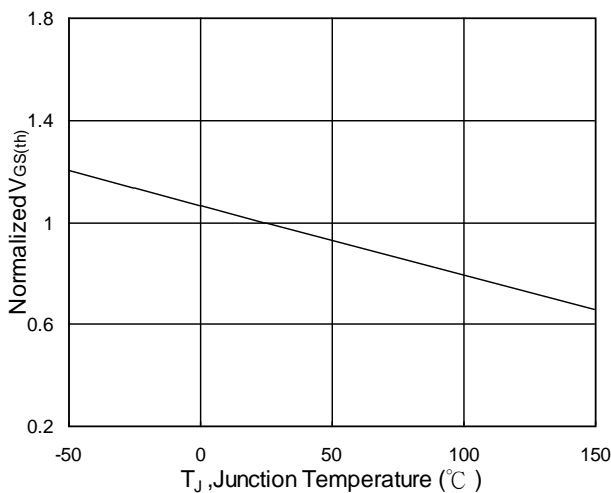


Fig.5 Normalized $V_{GS(th)}$ vs T_J

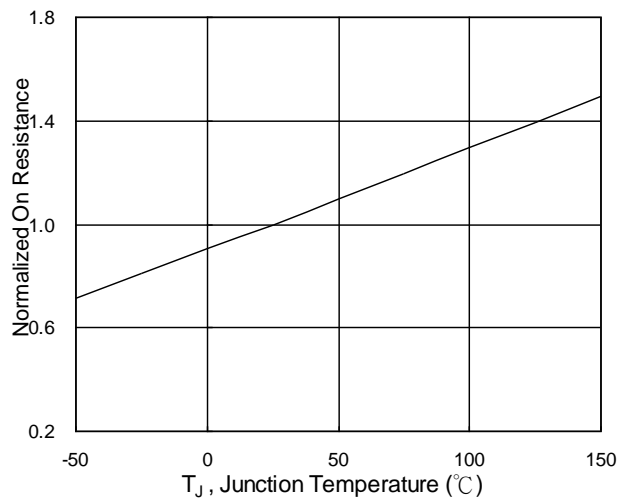


Fig.6 Normalized $R_{DS(on)}$ vs T_J

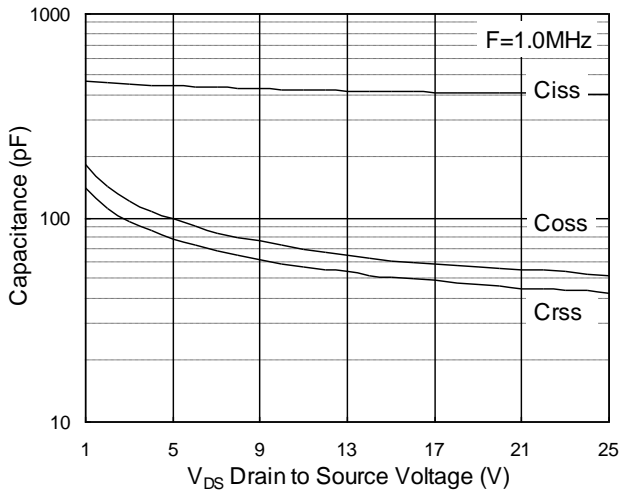


Fig.7 Capacitance

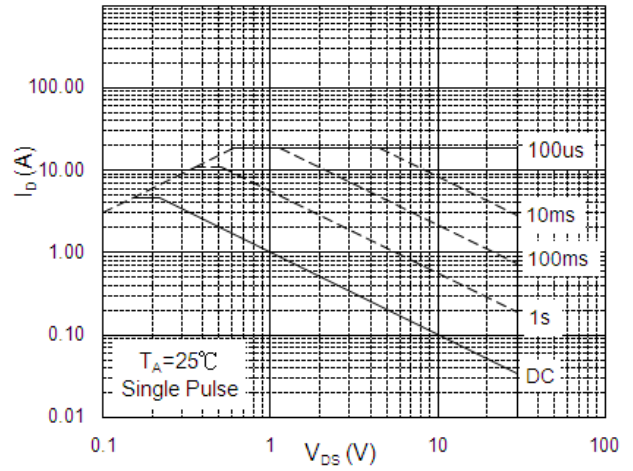


Fig.8 Safe Operating Area

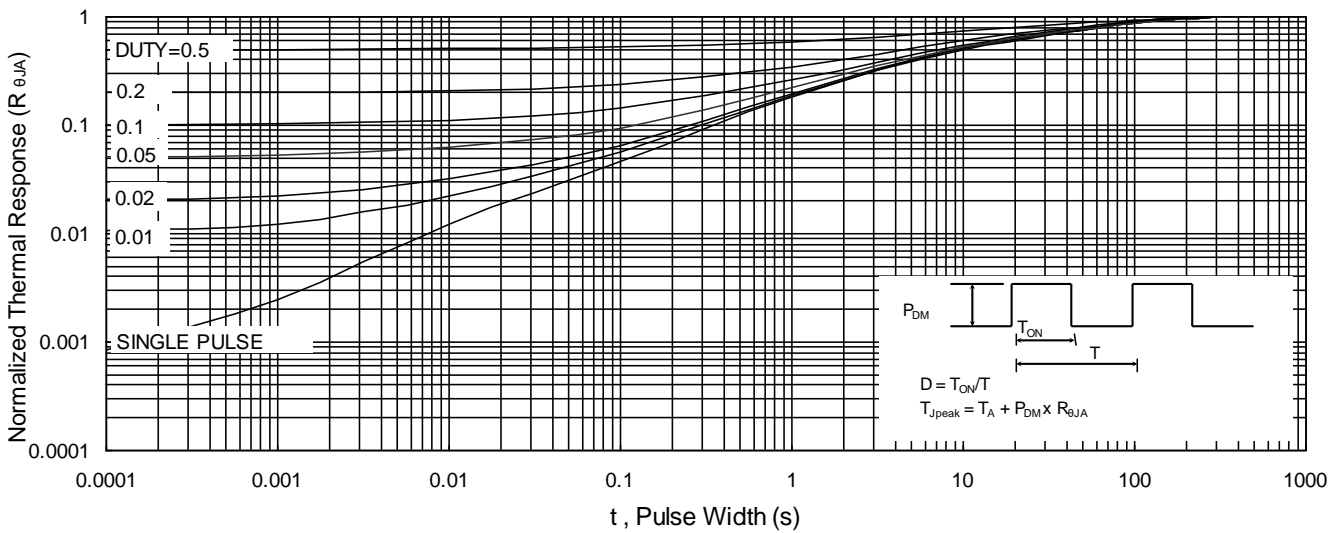


Fig.9 Normalized Maximum Transient Thermal Impedance

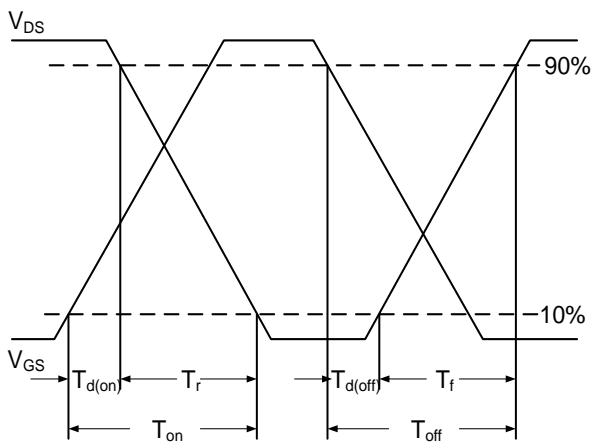


Fig.10 Switching Time Waveform

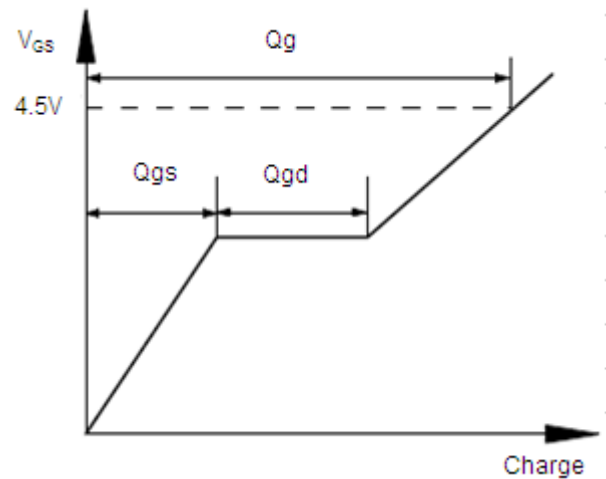


Fig.11 Gate Charge Waveform